

MA2B182

Silicon epitaxial planar type

For high-voltage switching circuits, small power rectification

■ Features

- High reverse voltage ($V_R = 200\text{ V}$)
- Large output current I_O
- DO-35 Package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Repetitive peak reverse voltage	V_{RRM}	250	V
Output current	I_O	200	mA
Repetitive peak reverse current	I_{FRM}	625	mA
Non-repetitive peak forward surge current surge current*	I_{FSM}	1	A
Average power dissipation	$P_{F(AV)}$	400	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

Note) * : $t = 1\text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200\text{ V}$			200	nA
Forward voltage (DC)	V_F	$I_F = 200\text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100\text{ }\mu\text{A}$	250			V
Terminal capacitance	C_t	$V_R = 0\text{ V}, f = 1\text{ MHz}$		4.5		pF

Note) Rated input/output frequency: 3 MHz

■ Cathode Indication

Type No.	MA2B182	
Color	1st Band	White
	2nd Band	Green



